



Si photodiodes

S1226 series

For UV to visible, precision photometry; suppressed near IR sensitivity

These Si photodiodes have suppressed IR sensitivity. They are suitable for low-light-level detection in analysis and the like.

Features

- Suppressed near IR sensitivity
- **■** High sensitivity in UV region (quartz glass type)
- Low dark current
- High reliability

Applications

- **■** Analytical equipment
- Optical measurement equipment, etc.

Structure / Absolute maximum ratings

Type no.	Dimensional			Absolute maximum ratings					
	Dimensional outline/		Photosensitive	Reverse	Operating	Storage			
	Window material* ¹	Package	area size	voltage	temperature	temperature			
				VR max	Topr	Tstg			
			(mm)	(V)	(°C)	(°C)			
S1226-18BQ*2	(1)/Q	TO-18	1.1 × 1.1		-20 to +60	-55 to +80			
S1226-18BK	(2)/K	10-16	1.1 ^ 1.1		-40 to +100	-55 to +125			
S1226-5BQ*2	(3)/Q		2.4 × 2.4		-20 to +60	-55 to +80			
S1226-5BK	(4)/K	TO-5	2.4 × 2.4	5	-40 to +100	-55 to +125			
S1226-44BQ*2	(5)/Q	10-5	3.6 × 3.6	5	-20 to +60	-55 to +80			
S1226-44BK	(6)/K		3.0 × 3.0		-40 to +100	-55 to +125			
S1226-8BQ*2	(7)/Q	TO-8	5.8 × 5.8		-20 to +60	-55 to +80			
S1226-8BK	(8)/K	10-0	J.0 X J.0		-40 to +100	-55 to +125			

^{*1:} Window material, K=borosilicate glass, Q=quartz glass

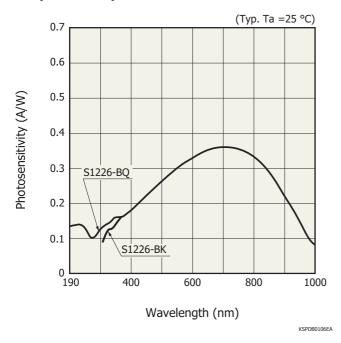
■ Electrical and optical characteristics (Typ. Ta=25 °C, unless otherwise noted)

Type no.	Spectral response range	Peak sensitivity wavelength λp	Photosensitivity S (A/W)			Short circuit current Isc		Dark current ID VR=10 mV	coefficient of ID	VR=0 V	Terminal capacitance Ct VR=0 V	Rsh		Noise equivalent power	
				200	nm	He-Ne laser			max.	nax. TCID	RL=1 kΩ	f=10 kHz	VR=10 mV		NEP
	(nm)	(nm)	λρ	Min.	Тур.	633 nm	Min. (μΑ)	Тур. (µА)	(pA)	(times/°C)	(µs)	(pF)	Min. (GΩ)	Typ. (GΩ)	(W/Hz ^{1/2})
S1226-18BQ	190 to 1000			0.10	0.12	0.34	0.5 0.66	2		0.15	35	5	50	1.6 × 10 ⁻¹⁵	
S1226-18BK	320 to 1000			-	-			0.00		1.12	0.13	33	,	30	1.0 ^ 10
S1226-5BQ	190 to 1000			0.10	0.12		2.2 2.9	2.0	2.9 5		0.5	160	2	20	2.5×10^{-15}
S1226-5BK	320 to 1000		0.26	-	-			2.9							2.5 × 10
S1226-44BQ	190 to 1000		0.36	0.10	0.12		4.4	5.9	10		1	500	1	10	3.6×10^{-15}
S1226-44BK	320 to 1000			-	-										3.6 × 10
S1226-8BQ	190 to 1000			0.10	0.12		12	16	20		2	1200	0.5	5	5.0 × 10 ⁻¹⁵
S1226-8BK	320 to 1000			-	-		12	10	20		2	1200	0.5	3	3.0 × 10

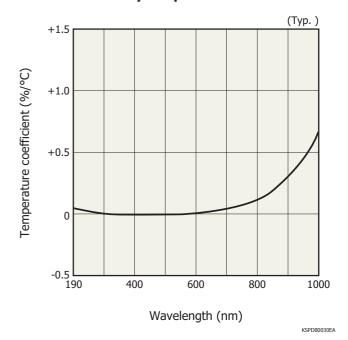
^{*2:} Refer to "Precautions against UV light exposure."

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

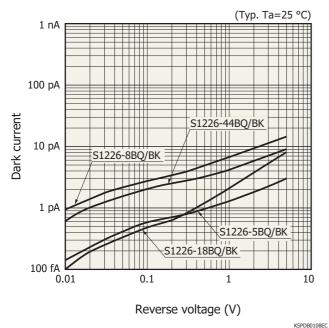
Spectral response



Photosensitivity temperature characteristic

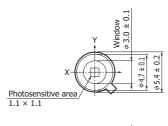


■ Dark current vs. reverse voltage



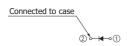
Dimensional outlines (unit: mm)

(1) S1226-18BQ





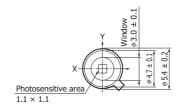


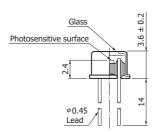


Distance from photosensitive area center to cap center $-0.3 \le X \le +0.3$ $-0.3 \le Y \le +0.3$

KSPDA0201EB

(2) S1226-18BK







Distance from photosensitive area center to cap center $-0.3 \le X \le +0.3$ $-0.3 \le Y \le +0.3$

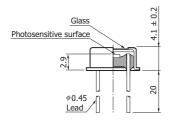
Connected to case

The glass window may extend a maximum of 0.2 mm above the upper surface of the cap.

KSPDA0113EE

(3) S1226-5BQ

Photosensitive area 2.4 × 2.4

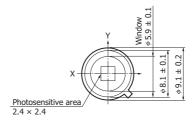


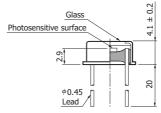


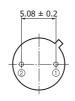
Connected to case

Distance from photosensitive area center to cap center $-0.3 \le X \le +0.3$ $-0.3 \le Y \le +0.3$

(4) S1226-5BK







Connected to case
② ──★── ①

Distance from photosensitive area center to cap center $-0.3 \le X \le +0.3$ $-0.3 \le Y \le +0.3$

The glass window may extend a maximum of 0.2 mm above the upper surface of the cap.

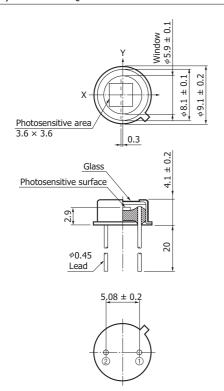
KSPDA0114ED



KSPDA0202FB

(5) S1226-44BQ

Connected to case

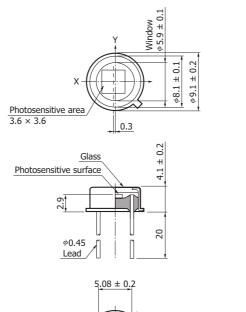


area center to cap center -0.6≤X≤0

Distance from photosensitive

-0.3≤Y≤+0.3

(6) S1226-44BK



Distance from photosensitive area center to cap center -0.6≤X≤0

-0.3≤Y≤+0.3



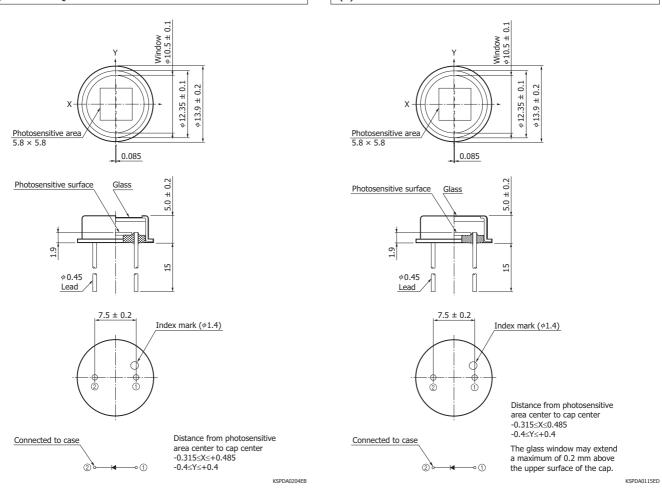
The glass window may extend a maximum of 0.2 mm above the upper surface of the cap.

KSPDA0195EC



(7) S1226-8BQ

(8) S1226-8BK



Precautions against UV light exposure

- · When UV light irradiation is applied, the product characteristics may degrade. Such examples include degradation of the product's UV sensitivity and increase in dark current. This phenomenon varies depending on the irradiation level, irradiation intensity, usage time, and ambient environment and also varies depending on the product model. Before employing the product, we recommend that you check the tolerance under the ultraviolet light environment that the product will be used in.
- Exposure to UV light may cause the characteristics to degrade due to gas released from the resin bonding the product's component materials. As such, we recommend that you avoid applying UV light directly on the resin and apply it on only the inside of the photosensitive area by using an aperture or the like.

Related information

www.hamamatsu.com/sp/ssd/doc_en.html

- Precautions
- · Disclaimer
- · Metal, ceramic, plastic package products
- Technical information
- · Si photodiode/Application circuit examples

Information described in this material is current as of October, 2015.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use. Copying or reprinting the contents described in this material in whole or in part is prohibited without our prior permission.

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